GMBCP56 NPN SILICON EPITAXIAL TRANSISTOR

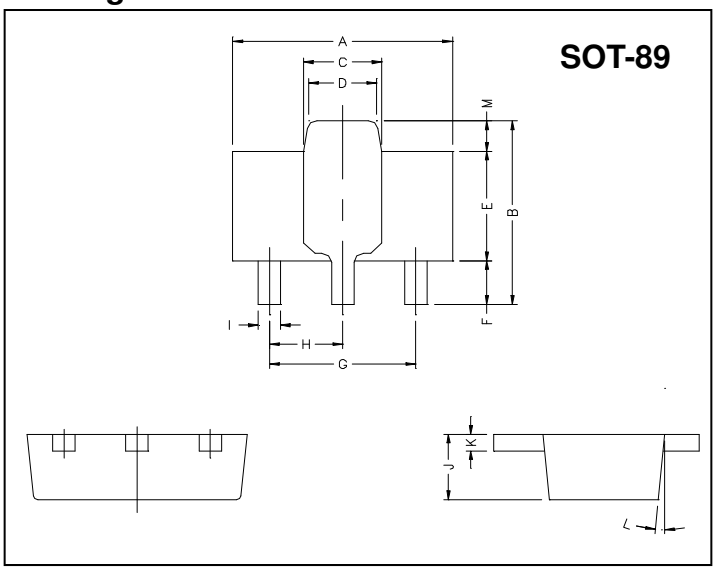
Description

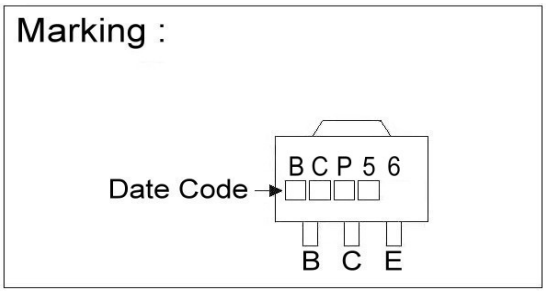
The GMBCP56 is designed for use in audio amplifiers and medium power amplifications.

Features

- Collector-Emitter Voltage: V_{CEO}=80V
- Complementary to GMBCX53

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00 REF.	
B	4.05	4.25	H	1.50 REF.	
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5° TYP.	
			M	0.70 REF.	

Absolute Maximum Ratings at Ta = 25℃

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature Range	T_{STG}	-65 ~ +150	℃
Collector to Base Voltage	V_{CBO}	100	V
Collector to Emitter Voltage	V_{CEO}	80	V
Emitter to Base Voltage	V_{EBO}	5	V
Collect Current(DC)	I_C	1	A
Total Power Dissipation	P_D	1.2	W

Electrical Characteristics (Ta = 25℃)

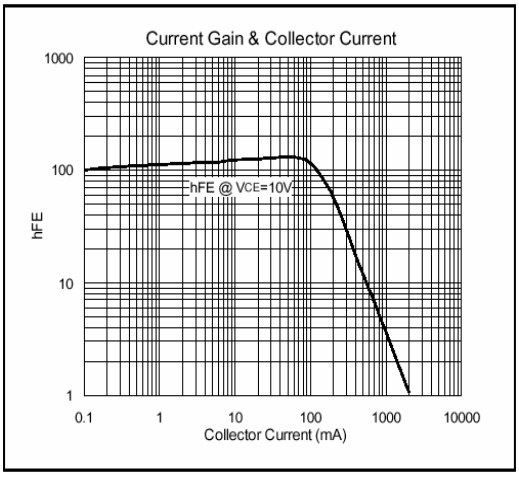
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	100	-	-	V	I_C=100uA, I_E=0
BV_{CEO}	80	-	-	V	I_C=1mA, I_B=0
BV_{EBO}	5	-	-	V	I_E=10uA, I_C=0
I_{CBO}	-	-	100	nA	V_{CB}=30V, I_E=0
I_{EBO}	-	-	100	nA	V_{EB}=5V, I_C=0
*$V_{CE(sat)}$1	-	-	500	mV	I_C=500mA, I_B=50mA
*$V_{BE(on)}$	-	-	1000	mV	I_C=500mA, V_{CE}=2V,
*h_{FE}1	63	-	-		V_{CE}=2V, I_C=5mA
*h_{FE}2	63	-	250		V_{CE}=2V, I_C=150mA
*h_{FE}3	40	-	-		V_{CE}=2V, I_C=500mA
fT	100	-	-	MHz	V_{CE}=5V, I_C=10mA

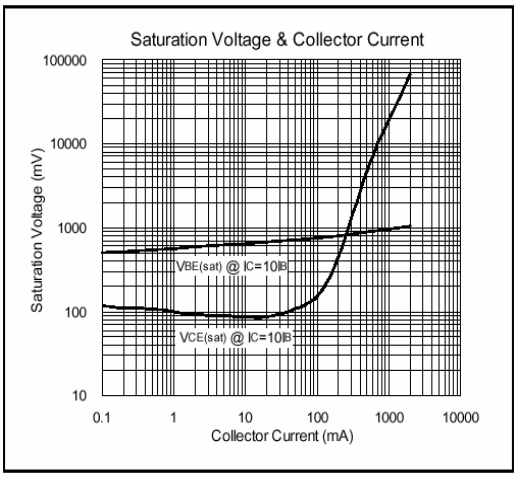
* Pulse Test: Pulse Width≦380μs, Duty Cycle≦2%

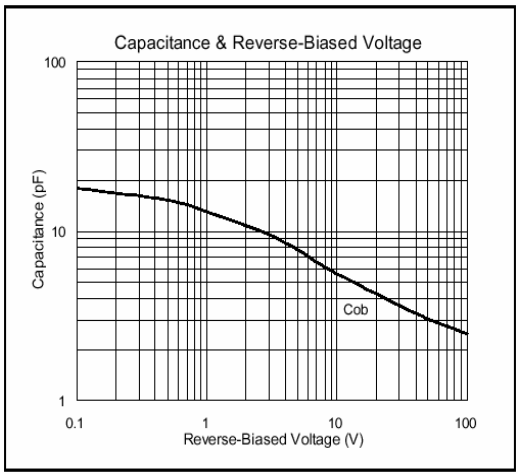
Classification Of h_{FE}2

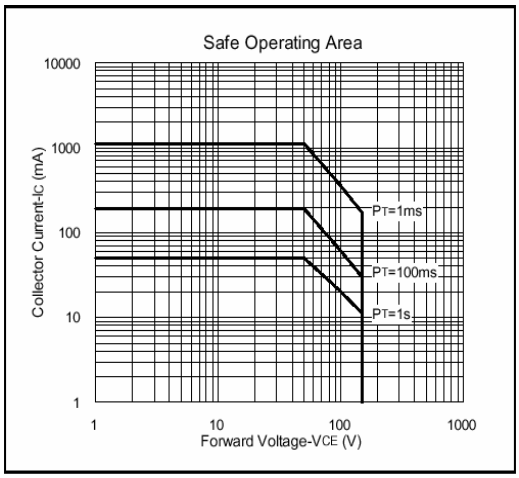
Rank	10	16
Range	63 - 160	100 - 250

Characteristics Curve









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